

Gas-Phase Ion-Molecule Chemistry of Methoxy-Substituted Silanes: Collision-Induced Decomposition of Siloxide Ions Leading to Anions of Silaacetaldehyde and Methyl Silaformate

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Methoxy-substituted silanes react with hydroxide in a tandem flowing afterglow selected ion flow tube to give a number of siloxide ions. Five of these, $(\text{CH}_3)_2(\text{CH}_3\text{O})\text{SiO}^-$, $(\text{CH}_3\text{O})_2(\text{H})\text{SiO}^-$, $(\text{CH}_3\text{O})_3\text{SiO}^-$, $\text{CH}_3(\text{CH}_3\text{O})(\text{H})\text{SiO}^-$, and $\text{CH}_3(\text{CH}_3\text{O})_2\text{SiO}^-$, have been submitted to collision-induced decomposition (CID) conditions. Three of these siloxides are suitable precursor ions for CH_3OSiO^- and CH_3SiO^- as well as an isomer of CH_3SiO^- which is the enolate of silaacetaldehyde. The chemistry of the siloxide ions has been studied by using N_2O , CO_2 , CS_2 , and COS as has that of many of the ions resulting from CID. The acidity of CH_3OSiO^- has been determined and compared with that of HSiO^- . The reported revision of the acidity of silaacetone takes account of up-to-date reference acidities.

Introduction

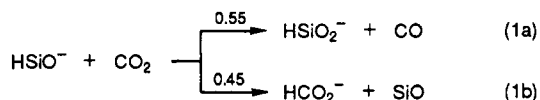
Multiple bonding to silicon has been studied in considerable detail over the past few years.¹ Much of the impetus for this work came from kinetic studies of the pyrolysis of dimethylsilacyclobutane carried out in the late 1960s. These studies strongly suggested the intermediacy of dimethylsilene, $[(\text{CH}_3)_2\text{Si}=\text{CH}_2]$. Interest was further fueled by the desire to compare various multiply bonded silicon species with their carbon analogues (e.g., $\text{Si}=\text{C}$ and $\text{Si}=\text{Si}$ with $\text{C}=\text{C}$, $\text{Si}=\text{O}$ with $\text{C}=\text{O}$, $\text{Si}=\text{N}$ with $\text{C}=\text{N}$, etc.). Our current state of knowledge of such silicon species derives from two fronts: one directed at determining the spectroscopic properties of these species in matrix isolation;^{1d} the other at preparing stable derivatives that are usually obtained by substituting the multiple bond with bulky groups.^{1e} These studies have generally indicated that multiple bonds to silicon are thermodynamically stable, although less so than their carbon analogues, and that such bonds are quite reactive, more so than their carbon analogues.

Despite the intense activity on multiply bonded silicon species, there is little experimental information on simply substituted species. We have approached this problem by studying the gas-phase ion-molecule chemistry of substituted silicon anions whose conjugate acids are related to simple silicon species. For example, we have previously studied SiCH^- and HSiO^- because of their relationship to silaacetylene and silanone.^{2,3} These two studies illustrate the approach we have taken as well as its advantages and limitations.

In studying the chemistry of SiCH^- , we have determined that the H is bonded to carbon rather than silicon and

found that this ion reacts as a carbon-centered nucleophile.² One of the limitations of our gas-phase methods is illustrated in measuring the acidity of the parent conjugate acid. Although such a measurement is easily made, the identity of the neutral parent compound is not always clear since the flowing afterglow (FA) technique detects only ionic species. The parent of SiCH^- could be either $\text{HSi}=\text{CH}$, $\text{H}_2\text{Si}=\text{C}$, or $\text{Si}=\text{CH}_2$. High-level ab initio computations strongly suggest that the most stable isomer is $\text{Si}=\text{CH}_2$.⁴

Detailed studies of HSiO^- have examined its fascinating reaction chemistry, where, for example, it reacts with CO_2 in both an oxidative and a reductive channel (eq 1).³ In



addition, we have been able to determine the heats of formation of both HSiO^- and its conjugate acid. Here again, we have the limitation of not knowing the structure of the neutral, which could be either $\text{H}_2\text{Si}=\text{O}$ or HSiOH . The several computational studies published on these isomers suggest only very small energetic differences with HSiOH more stable by just a few kcal/mol.^{3,5} Computations at a higher level indicate that $\text{H}_2\text{Si}=\text{O}$ is more stable than HSiOH by 2.7 kcal/mol [MP2/6-31G(d,p) geometries and MP4/MC-311G(d,p) energies corrected for zero-point vibrational energies].⁶

In the studies reported here, we have extended our HSiO^- work to anions related to CH_3SiHO and HSiO_2CH_3 , the silicon analogues of acetaldehyde and methyl formate, respectively. This study addresses questions about their synthesis by collision-induced decomposition (CID) of various methoxy-substituted siloxide ions, about their reactivity and structure, and about their thermochemistry.

Experimental Section

All experiments were carried out at room temperature in a flowing afterglow selected ion flow tube (FA-SIFT) which has been

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(5) (a) Kudo, T.; Nagase, S. *Organometallics* **1986**, *5*, 1207. (b) Kudo, T.; Nagase, S. *Chem. Phys. Lett.* **1986**, *128*, 507. (c) Kudo, T.; Nagase, S. *J. Am. Chem. Soc.* **1985**, *107*, 2589. (d) Kudo, T.; Nagase, S. *J. Phys. Chem.* **1984**, *88*, 2833. (e) Kudo, T.; Nagase, S. *J. Organomet. Chem.* **1983**, *253*, C23. (f) Gordon, M. S.; George, C. *J. Am. Chem. Soc.* **1984**, *106*, 609.

(6) Gordon, M. S.; Peterson, L. A. *J. Phys. Chem.*, submitted.

(1) *The Chemistry of the Functional Groups: The Chemistry of Organic Silicon Compounds*; Patai, S., Rappoport, R. I., Eds.; Wiley: New York, 1989. These two volumes, which have just been published, are likely to set the standard as a general reference work on organosilicon chemistry for years to come. More specific references to multiply bonded silicon species follow: (a) Raabe, G.; Michl, J. In *The Chemistry of the Functional Groups: The Chemistry of Organic Silicon Compounds*; Patai, S., Rappoport, R. I., Eds.; Wiley: New York, 1989; Chapter 17. (b) Gusev, L. E.; Nametkin, N. S. *Chem. Rev.* **1979**, *79*, 529. (c) Bertrand, G.; Trinquier, G.; Mazerolles, P. *J. Organomet. Chem. Libr.* **1981**, *12*, 1. (d) Wiberg, N. *J. Organomet. Chem.* **1984**, *273*, 141. (e) Raabe, G.; Michl, J. *Chem. Rev.* **1985**, *85*, 419. (f) Brook, A. G.; Baines, K. M. *Adv. Organomet. Chem.* **1986**, *29*, 1.

(2) Damrauer, R.; DePuy, C. H.; Barlow, S. E.; Gronert, S. *J. Am. Chem. Soc.* **1988**, *110*, 2005. For initial observations of collisional activation in a SIFT instrument, see: Henchman, M.; Viggiano, A. A.; Paulson, J. F.; Freedman, A.; Wormhoudt, J. *J. Am. Chem. Soc.* **1985**, *107*, 1453.

(3) Gronert, S.; O'Hair, R. A.; Prodnuck, S.; Sülzle, D.; Damrauer, R.; DePuy, C. H. *J. Am. Chem. Soc.* **1990**, *112*, 997.

described in detail previously.⁷ A brief description of the technique follows. The FA-SIFT consists of four sections: a source flow tube for ion preparation (A), an ion separation and purification region (B), a second flow tube for studying the chemical reactions of the selected ions (C), and finally an ion detection region (D). In the first flow tube (A) oxide ions (O^-) are prepared by electron ionization of small amounts of N_2O (0.01 Torr) entrained in a rapidly flowing (40 m/s) helium stream (0.4 Torr), and these are rapidly converted to hydroxide ions by hydrogen atom abstraction from 0.02 Torr of methane also entrained in the helium. Downstream various silanes are added through a moveable inlet, and rapid reactions ensue, producing a variety of ionic products.

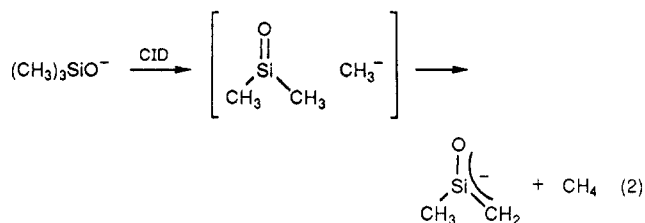
At the end of the first flow tube the ions are sampled through a 2-mm orifice into the ion separation region (B), and the helium and other neutrals are removed by pumping, while the ions are focused into a quadrupole mass filter by a series of electrostatic lenses. This SIFT quadrupole is tuned to an appropriate m/z , and the desired ion is injected into the second flow tube (C), where it is again entrained in helium (0.5 Torr). At the end of the second flow tube ions are sampled through a 0.5-mm orifice, mass analyzed, and detected by an electron multiplier.

To inject ions from the low-pressure (10^{-6} Torr) region of the SIFT quadrupole into the higher pressure region of the second flow tube, they must be extracted by an electrical potential. This potential imparts kinetic energy to the ions, which is removed by multiple collisions with the helium buffer gas. If this potential is made sufficiently high, ions can undergo collision-induced dissociation (CID) to form new ions. In a field-free region, the resulting ions subsequently undergo multiple collisions with helium and are usually cooled to room temperature before being allowed to react with neutral reagents. The injection potential leading to decomposition of ions is the potential difference between the ion source and the injector plate. The resulting exact kinetic energy of the ions is a sensitive function of a variety of factors and, thus, is not well characterized.

All reactions were studied at 300 K at a helium buffer gas pressure of 0.5 Torr and a flow of 250 STP $cm^3 s^{-1}$. Branching ratios were determined as a function of reaction distance and are reported as extrapolations to zero reaction distance to eliminate any effects of differential diffusion among the ions and of secondary reactions. Gases were obtained from commercial sources and were of the following purities: He (99.995%), N_2O (99.99%), O_2 (99.95%), CH_4 (99.99%), CO_2 (99.5%), SO_2 (99.9%), and COS (97.7%). Other reagents also were obtained from commercial sources and were purified as necessary before use. The helium buffer gas was passed through a liquid nitrogen cooled molecular sieve trap before entering the flow tubes.

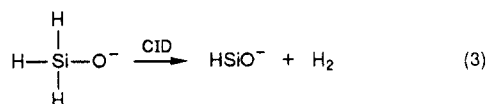
Results and Discussion

Many of the likely pathways for CID of siloxide ions have been recently explored by Squires, Bowie, and co-workers.^{8,9} Squires seminal work carried out by FTMS techniques described the decomposition of $(CH_3)_3SiO^-$, which yielded silacetone enolate and methane (eq 2), presumably following the path illustrated.⁸ More recently, Bowie has described the CID behavior of a number of siloxides [$(CH_3)_3SiO^-$, $(CH_3)_2HSiO^-$, $(CH_3)_2(CH_3CH_2)SiO^-$, $(CH_3CH_2)_3SiO^-$, $(CH_3CH_2)_2HSiO^-$, $(CH_3)_2(CH_2=CHC-$

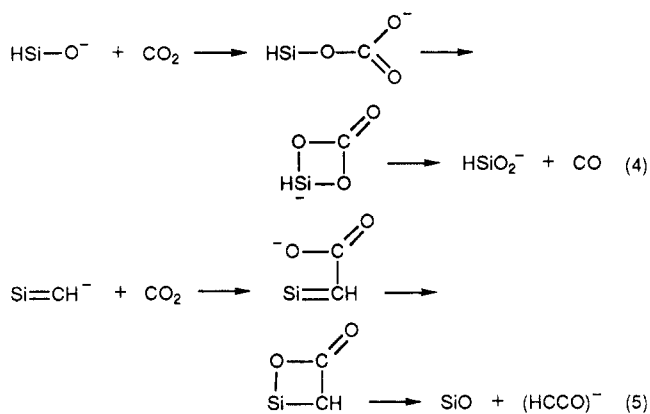


$H_2)SiO^-$, $(CH_3)_2(CH_2=CH)SiO^-$, and $(C_6H_5)_3SiO^-$].⁹ In addition, ab initio computations on the silacetone anion and CH_3SiO^- have been reported.⁹

With our recent observation that CID experiments could be carried out in the flowing afterglow selected ion flow tube (FA-SIFT),³ we realized that many of the tremendous variety of interesting ions that could be produced in the FA source could be collisionally decomposed and that subsequent reactions using conventional FA techniques could probe their identity and reactivity. Thus, FA-SIFT has a potentially significant advantage over other techniques since the chemistry of the ions produced by CID can be studied in detail, as our recent study of $HSiO^-$ illustrates very well. This anion has been prepared by CID of H_3SiO^- (eq 3). Its chemistry has been probed by using



CO_2 , COS, CS_2 , SO_2 , O_2 , acetic acid, nitromethane, and hexafluorobenzene and is largely dominated by two factors: its high nucleophilic reactivity at oxygen (eq 1a) and its hydride-donating tendencies (eq 1b). A number of the reactions of $HSiO^-$, as well as those of $SiCH^-$, are reasonably explained by mechanisms involving four-membered intermediates (eqs 4 and 5).



In this study we have further realized the potential of the CID FA-SIFT technique by examining the decomposition of several new siloxides. We also have examined the effect of methoxy substituents on silicon since Bowie and co-workers¹¹ had previously reported a number of interesting examples of ion-molecule chemistry involving methoxysilanes. Finally, we explore more complex silicon compounds having the potential for multiple reaction pathways.

Reactions of Methoxysilanes with Hydroxide: Siloxide Ion Formation. We have examined the reaction of hydroxide with trimethylmethoxysilane, dimethyldimethoxysilane, trimethoxysilane, and methyldimethoxy-

(7) Van Doren, J. M.; Barlow, S. E.; DePuy, C. H.; Bierbaum, V. M. *Int. J. Mass Spectrom. Ion Proc.* **1987**, *81*, 85.

(8) Froelicher, S. W.; Freiser, B. S.; Squires, R. R. *J. Am. Chem. Soc.* **1984**, *106*, 6863.

(9) O'Hair, R. A.; Bowie, J. H.; Currie, G. *J. Aust. J. Chem.* **1988**, *41*, 57.

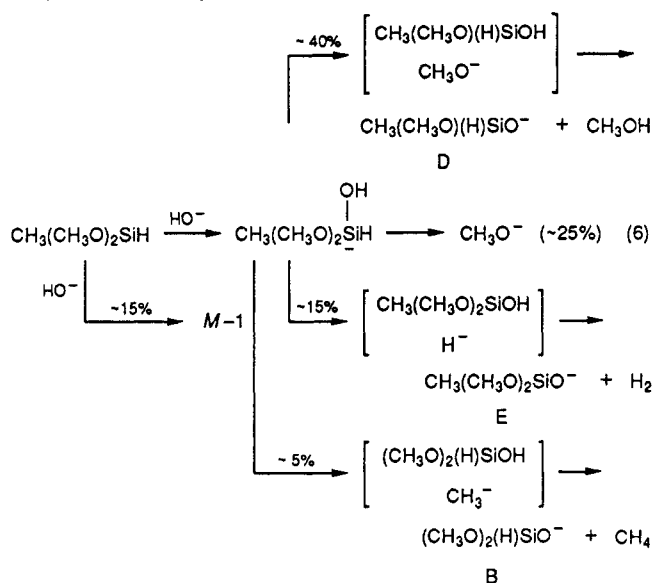
(10) We have used a bracket notation throughout this paper to represent ion-molecule product complexes. The more common notation of enclosing intermediates in brackets has not been used to avoid confusion. The sense of the text makes it clear when intermediate species are being represented in the equations. We have used the term "ion-molecule product complex" to describe those complexes formed as the result of either the decomposition of a silicate or the CID of a siloxide. This terminology distinguishes such cases from collision complexes that result when a reactant ion and a neutral collide. We thank one of the referees for suggesting that we emphasize these differences.

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Table I. Reactions of Hydroxide and Methoxysilanes

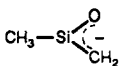
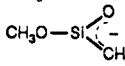
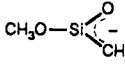
reactant	products
(CH ₃) ₃ SiOCH ₃	M - 1 (≈10%) CH ₃ O ⁻ (≈55%) (CH ₃) ₃ SiO ⁻ (≈25%) (CH ₃) ₂ (CH ₃ O)SiO ⁻ (≈10%) (A)
(CH ₃) ₂ Si(OCH ₃) ₂	M - 1 (≈15%) CH ₃ O ⁻ (≈20%) (CH ₃) ₂ (CH ₃ O)SiO ⁻ (≈50%) (A) (CH ₃)(CH ₃ O) ₂ SiO ⁻ (≈15%) (E)
(CH ₃ O) ₃ SiH	M - 1 (≈10%) CH ₃ O ⁻ (≈35%) (CH ₃ O) ₂ (H)SiO ⁻ (≈40%) (B) (CH ₃ O) ₃ SiO ⁻ (≈15%) (C)
CH ₃ (CH ₃ O) ₂ SiH	M - 1 (≈15%) CH ₃ O ⁻ (≈25%) CH ₃ (CH ₃ O)(H)SiO ⁻ (≈40%) (D) CH ₃ (CH ₃ O) ₂ SiO ⁻ (≈15%) (E) (CH ₃ O) ₂ (H)SiO ⁻ (≈5%) (B)

silane. The products from these reactions are compiled in Table I. Of particular importance to this work is the formation of various siloxide ions from these methoxysilanes. Siloxide ion formation is consistent with a mechanism previously suggested in which hydroxide adds to tetracoordinate silicon to form a pentacoordinate anionic intermediate (siliconate).¹² Since this is a highly exothermic addition,¹³ the resulting intermediate cannot be stabilized by collision and fragments to give an ion-molecule product complex¹⁰ of a tetracoordinate silanol and a basic anion (in these cases, methoxide, hydride, and/or methide). Before the basic anion can escape the ion-molecule product complex, it abstracts the SiO-H proton, giving a siloxide. Equation 6 illustrates the proposed pathways leading to the products for the most complex example we have studied, the reaction of methyl dimethoxysilane and hydroxide.



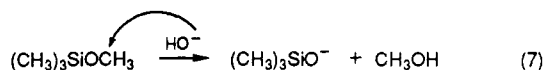
In eq 6 the three siloxides result from the same pentacoordinate intermediate, [CH₃(CH₃O)₂(H)SiOH]⁻. This intermediate fragments to give ion-molecule product complexes of methylmethoxysilanol and methoxide, methyl dimethoxysilanol and hydride, and dimethoxysilanol and methide ion. The three resulting siloxides are then formed in amounts at least partially controlled by the

Table II. Collision-Induced Decomposition of Siloxides A-E

reactant	products (<i>m/z</i>)
(CH ₃) ₂ (CH ₃ O)SiO ⁻ (A)	 (73) (CH ₃) ₂ (H)SiO ⁻ (75) or CH ₃ SiO ₂ ⁻ (75) [see text]
(CH ₃ O) ₂ (H)SiO ⁻ (B)	CH ₃ OSiO ⁻ (75) (CH ₃ O)(H)(HO)Si ⁻ (77) or (CH ₃ O)(H) ₂ SiO ⁻ (77) [see text]
(CH ₃ O) ₃ SiO ⁻ (C)	CH ₃ OSiO ⁻ (75) (CH ₃ O) ₂ (HO)Si ⁻ (107)
(CH ₃ O)(CH ₃)(H)SiO ⁻ (D)	CH ₃ SiO ⁻ (59) -CH ₂ SiHO (59) CH ₃ (H) ₂ SiO ⁻ (61) or CH ₃ (H)(HO)Si ⁻ (61) [see text] CH ₃ OSiO ⁻ (75)  (89)
CH ₃ (CH ₃ O) ₂ SiO ⁻ (E)	 (89) CH ₃ (CH ₃ O)(HO)Si ⁻ (91) or CH ₃ (CH ₃ O)(H)Si ⁻ (91) [see text]

basicity of the anionic component of these ion-molecule product complexes. We have shown in studies on alkane acidities that the less basic anions are more readily cleaved from silicon;¹² here, in much the same way, the ion-molecule product complex containing methoxide is expected to predominate over that containing hydride over that containing methide as the branching ratios indicate. Such an explanation holds equally well for the other three reactions recorded in Table I.

In each of the four reactions with hydroxide, the product that arises from methoxide cleavage might result from an alternate mechanism to the one just proposed. S_N2 reaction of hydroxide at the methyl of the methoxy groups would lead to siloxide product directly (eq 7). We have



studied this possibility by using ¹⁸O-labeled HO⁻ in reactions with (CH₃)₂Si(OCH₃)₂ and (CH₃)₃SiOCH₃ and have evidence that both S_N2 reaction and association to a pentacoordinate silicate are occurring simultaneously, although this cannot be quantified.

In summarizing the reactions of the methoxysilanes with hydroxide, the predominant reaction path involves the formation of a pentacoordinate silicon anion (siliconate) from which methoxide formation results. With the exception of the M-1 products (10-15)% and that amount of S_N2 reaction occurring, the rest of the products form from their respective siliconates.

Collision-Induced Decomposition of Siloxides: Product Identification Studies. Siloxide ions A-E (Table I) undergo collision-induced decomposition (CID) to the products given in Table II.

An ion such as A potentially can decompose in several ways. We suggest that the *m/z* = 73 ion that forms is silacetone enolate resulting from a complex of silacetone and methoxide by a process analogous to that illustrated in eq 2. Four *m/z* = 75 possibilities exist; two of these could result from a complex of methyl silacetate and methide (eq 8). In one, CH₃OSiO⁻ could form when methide attacks the methyl group attached to silicon thus forming ethane (eq 8a). The other decomposition could lead to silacetate and ethane from methide attack at the

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